

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A low-reflectance conductive film characterized in that said low-reflectance conductive film comprises at least two films which are a conductive film comprising conductive fine particles and a low-refraction film formed on said conductive film, having a lower refractive index than said conductive film, and that said conductive film comprises a resistance-lowering material;

wherein the resistance-lowering material comprises a sulfur compound and/or titanium oxide;

wherein the sulfur compound is selected from the group consisting of α -lipoic acid, α -lipoamide, thiodipropionic acid, sodium thiosulfate, and sodium thioglycollate; and

wherein the content of the titanium oxide in the conductive film is from 0.1 to 20 mass % to the conductive fine particles in the conductive film.

Claim 2 (Original): The low-reflectance conductive film according to Claim 1, wherein said conductive fine particles are fine particles of tin-doped indium oxide or fine particles of antimony-doped tin oxide.

Claims 3-4 (Canceled).

Claim 5 (Currently Amended): The low-reflectance conductive film according to Claim 1, wherein said resistance-lowering material ~~is a~~ comprises the sulfur compound, and the content of said sulfur compound in said conductive film, when converted to the mass of sulfur in said conductive film, is from 0.1 to 10 mass% to the conductive fine particles in the conductive film.

Claim 6 (Currently Amended): The low-reflectance conductive film according to Claim 1, wherein said resistance-lowering material ~~is~~ comprises titanium ~~oxide. oxide, and~~
~~the content of said titanium oxide in the conductive film is from 0.1 to 20 mass% to the~~
~~conductive fine particles in the conductive film.~~

Claim 7 (Original): The low-reflectance conductive film according to Claim 1,
wherein said conductive film has a film thickness of from 5 to 200 nm, and said low-
refraction film has a film thickness of from 5 to 150 nm.

Claim 8 (Currently Amended): A colored low-reflectance conductive film which
comprises
the low-reflectance film according to Claim 1 and Claim 1, wherein
a colored film containing therein a coloring component which is formed on a side
opposite to the low refraction film of said conductive film.

Claim 9 (Original): The colored low-reflectance conductive film according to Claim
8, wherein said coloring component is carbon black or titanium black.

Claim 10 (Original): The colored low-reflectance conductive film according to Claim
8, wherein said colored film has a film thickness of from 5 to 200 nm.

Claim 11 (Original): A coated article comprising a substrate on which there is formed
said low-reflectance conductive film as defined in Claim 1.

Claim 12 (Original): A display apparatus wherein said coated article as defined in Claim 11 is incorporated so as to position said low-reflectance conductive film or said colored low-reflectance conductive film at an external surface thereof.

Claim 13 (Currently Amended): An X-coating liquid comprising a solvent, conductive fine particles, and a resistance-lowering material;
wherein the resistance-lowering material comprises a sulfur compound and/or titanium oxide;

wherein the sulfur compound is selected from the group consisting of α -lipoic acid, α -lipoamide, thiodipropionic acid, sodium thiosulfate, and sodium thioglycollate; and

wherein the content of the titanium oxide in the conductive film is from 0.1 to 20 mass % to the conductive fine particles in the conductive film.

Claim 14 (Currently Amended): A conductive film forming coating liquid as defined in Claim 13, wherein the concentration of said conductive fine particles is from 0.01 to 20 mass% to the total mass of said coating liquid liquid, and

wherein said resistance-lowering material is a comprises titanium oxide, source, and
~~the content of said titanium oxide source, when converted to the mass of titanium oxide, is from 0.1 to 20 mass% to the conductive fine particles.~~

Claim 15 (Currently Amended): A low-refraction film forming coating liquid comprising a solvent, a silicon compound, and a resistance-lowering material comprises a sulfur compound and/or titanium oxide;

wherein the resistance-lowering material comprises at least one compound selected from the group consisting of α -lipoic acid, α -lipoamide, thiodipropionic acid, sodium thiosulfate, and sodium thioglycollate; and

wherein content of the titanium oxide in the conductive film is from 0.01 to 1.0 mass % to the total amount of said low-refraction film forming coating liquid.

Claim 16 (Currently Amended): The low-refraction film forming coating liquid according to Claim 15, wherein said silicon compound is a silicon alkoxide, with the content of said silicon alkoxide being in an amount of from 0.1 to 30 mass% in terms of the solid component concentration of SiO_2 to the total amount of said low-refraction film forming coating liquid, and said resistance-lowering material ~~is a~~ comprises the sulfur compound, with the content of said sulfur compound being in an amount of from 0.01 to 1.5 mass% to the total amount of said low-refraction film forming coating liquid.

Claim 17 (Currently Amended): The low-refraction film forming coating liquid according to Claim 15, wherein said silicon compound is a silicon alkoxide, with the content of said silicon alkoxide being in an amount of from 0.1 to 30 mass% in terms of the solid component concentration of SiO_2 to the total amount of said low-refraction film forming coating liquid, and said resistance-lowering material ~~is a~~ comprises titanium oxide.

~~source, with the content of said titanium oxide source, when converted into the amount of titanium oxide, being in an amount of from 0.01 to 1.0 mass% to the total amount of said low-refraction film forming coating liquid.~~

Claim 18 (Currently Amended): A low-reflectance conductive film manufacturing method for forming a low-reflectance film which comprises: ~~by~~

coating onto a substrate a conductive film forming coating liquid which contains conductive fine particles, and then

coating a low-refraction film forming coating liquid which contains a resistance-lowering material;

wherein the resistance-lowering material comprises at least one compound selected from the group consisting of α -lipoic acid, α -lipoamide, thiodipropionic acid, sodium thiosulfate, sodium thioglycollate, and 0.1 to 20 mass% of titanium dioxide.

Claim 19 (Currently Amended): ~~A colored~~ The low-reflectance film manufacturing method according to Claim 18 which further comprises ~~for forming a colored low-reflectance film by~~

coating onto ~~[[a]]~~ the substrate a colored film forming coating liquid which contains a coloring component, prior to the coating of said conductive film forming coating liquid.

Claim 20 (Currently Amended): A low-reflectance conductive film manufacturing method, which comprises: ~~characterized by~~

coating onto a substrate a conductive film forming coating liquid which contains conductive fine particles, then

coating a low-refraction film coating liquid, thereby forming a low-reflectance conductive film, and

irradiating said low-reflectance conductive film with a light having energy greater than the band gap of said conductive particles, thereby reducing the surface resistance value of said low-reflectance film in comparison with the case where the irradiation of said light is not carried out;

wherein the conductive fine particles comprise a resistance-lowering material comprising a sulfur compound and/or titanium oxide;

wherein the sulfur compound is selected from the group consisting of α -lipoic acid, α -lipoamide, thiodipropionic acid, sodium thiosulfate, and sodium thioglycollate; and

wherein the content of the titanium oxide in the conductive film is from 0.1 to 20 mass % to the conductive fine particles in the conductive film.

Claim 21 (Currently Amended): A low-reflectance conductive film manufacturing method for forming a low-reflectance conductive film which comprises: by

coating onto a substrate a conductive film forming coating liquid which contains conductive fine particles, then

coating a low-refraction film forming coating liquid, thereby forming the low-refraction film, ~~characterized in that~~

wherein said conductive film forming coating liquid and/or said low-refraction film forming coating liquid contains a titanium oxide source, and the surface resistance value of said low-reflectance film is reduced by irradiating said low-reflectance conductive film with light having energy greater than the band gap of titanium oxide, in comparison with the case where the irradiation of said light is not carried out;

wherein content of the titanium oxide source in said conductive film forming coating liquid and/or said low-refraction film forming coating liquid is from 0.01 to 1.0 mass % to the total amount of said conductive film forming coating liquid and/or said low-refraction film forming coating liquid.

DISCUSSION OF AMENDMENT

Claims 1-21 are pending.

Claims 1, 13, and 15 are amended to include the limitations contained in original Claims 3-4 and 6 except that "thiourea" in Claim 4 has been excluded from the Markush group of sulfur-containing compounds.

Claim 18 is amended to include the limitations containing in original Claims 3-4 except that "thiourea" in Claim 4 has been excluded from the Markush group of sulfur-containing compounds.

Claims 20-21 are amended to include the limitations of at least one of Claims 3-4 and 6.

Claims 3-4 are canceled without prejudice.

Claims 5, 8, 14, 16-17, 19, and 21 are amended in order to improve readability.

No new matter is believed to be added upon entry of the amendment.

Upon entry of the amendment, Claims 1-2 and 5-21 will be active.